

<b>Semiconductor</b>	SiC
<b>Poly-Type</b>	4H
<b>Diameter</b>	150 mm



**Table Epitaxy Layer Specifications**

Items	N-type Specification
Diameter	150mm
Poly-type	4H
Primary flat orientation	[11-20] ± 5.0°
Orientation	Off axis: 4° toward <11-20>±0.5°
Conductivity	N Type
Dopant	Nitrogen
Net doping density	N <sub>D</sub> -N <sub>A</sub>
Carrier Concentration	1E14-1E19/cm <sup>3</sup>
Carrier Concentration Tolerance	±20%
Thickness	0.2~100um
Thickness Tolerance	±10% of selected thickness
TUA (Total Usable Area, 3mm*3mm, EE=3mm)	≥90%
Scratches (Front side)	Cumulative length ≤1X wafer diameter
Backside cleanliness	95% clean

Notes:

N-type epi layers ≤ 30 microns are preceded by an n-type, 1E18 cm<sup>-3</sup>, 0.5-1 um buffer layer.

Carrier Concentration is determined as an average value across the wafer using Hg probe CV.

Epi Thickness is determined as an average value across the wafer using FTIR.

For ultra high thickness above 30 μm or any special epitaxy requests, please contact our Sales.

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## Contact info

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